

**IN THE DRAWINGS:**

Applicants respectfully request approval of the following drawing changes. Figures 1 and 4 are being amended to label RF Shield “10a” in accordance with the specification. Applicants hereby submit an “Annotated Copy” of Figures 1 and 4 showing the requested change in red permanent ink, and a “Replacement Sheet” incorporating the change to Figures 1 and 4. No new matter has been added.

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FIG. 1

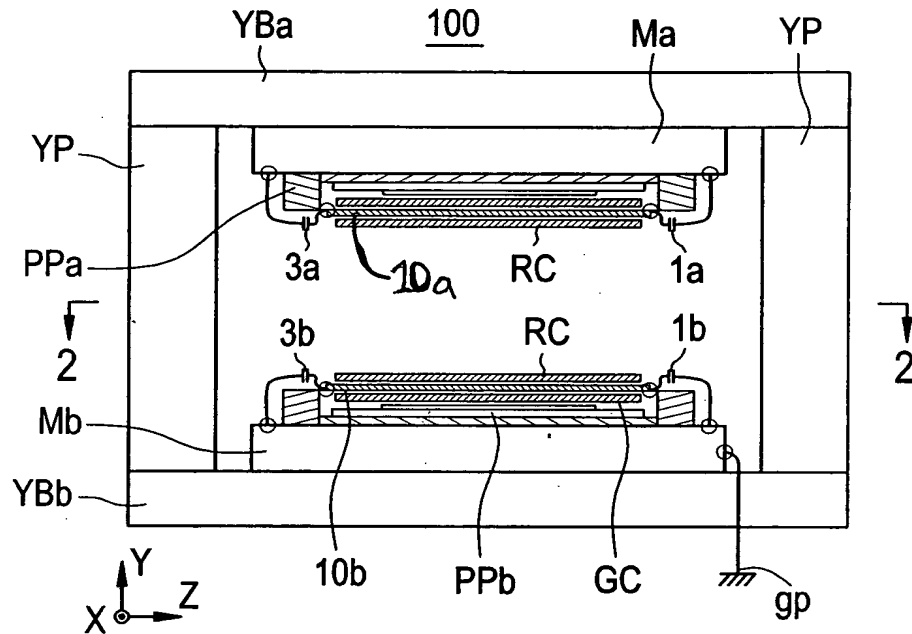
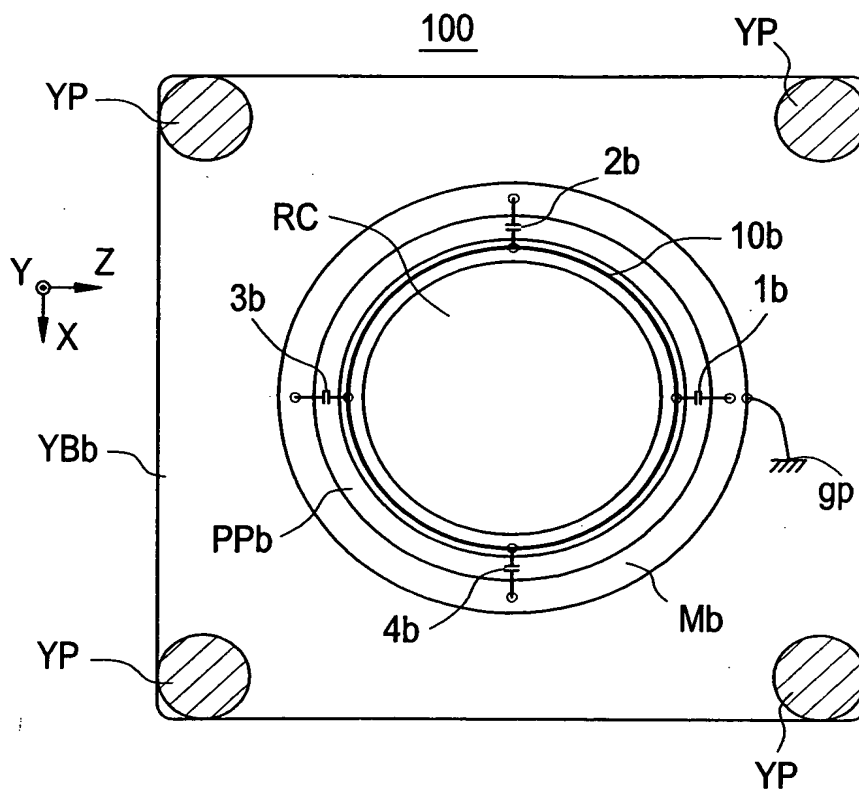


FIG. 2



The diagram illustrates a semiconductor device 200 with two stacked semiconductor elements, 10a and 10b. Element 10a (top) consists of a p-type layer 3a, an n-type layer 1a, and a resistor 10a. Element 10b (bottom) consists of a p-type layer 3b, an n-type layer 1b, and a resistor 10b. The device is mounted on a substrate 200 with various layers: YBa, Ma, YP, PPa, PPb, Mb, and YBb. A ground connection gp is shown at the bottom right.

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FIG. 1

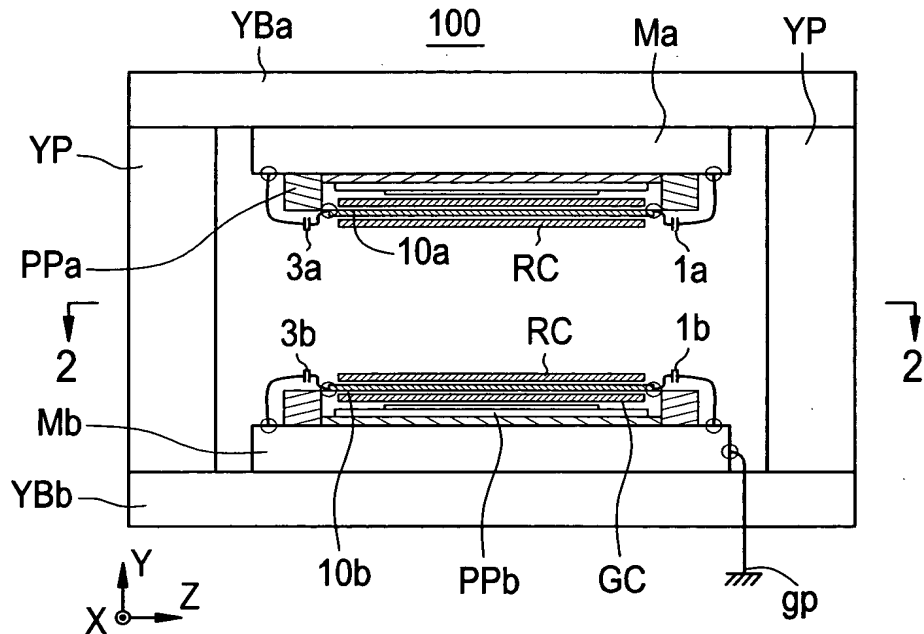
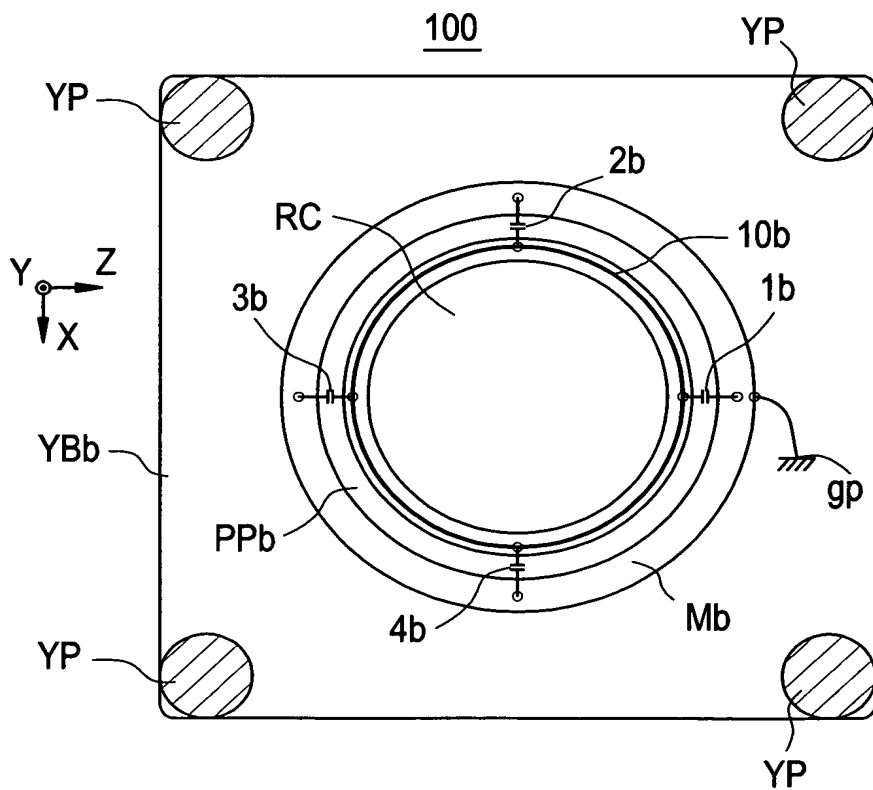


FIG. 2



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FIG. 3

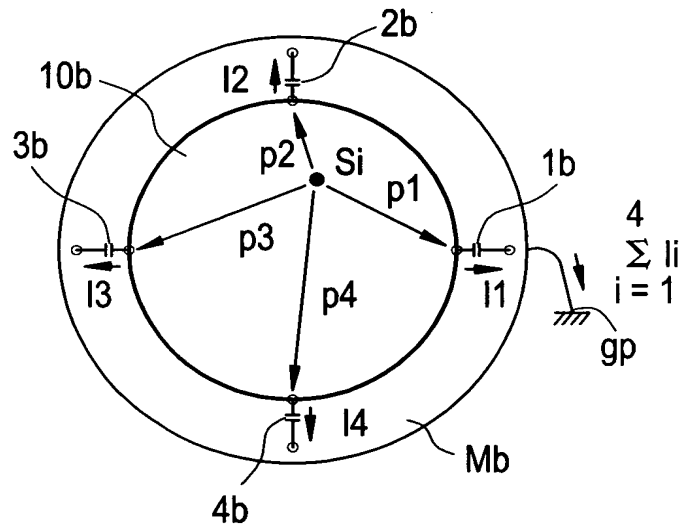


FIG. 4

